

Supporting Information

The Influence of Interlayer Bias and Crystal Field on the Electronic Characteristics of Twisted Tri-layer Graphene

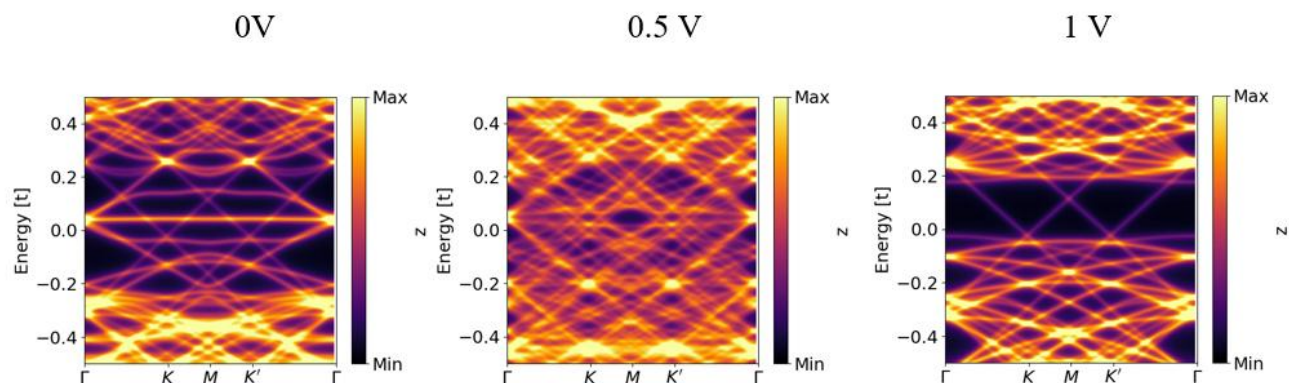
Mufasila Mumthaz Muhammed¹ and Junais Habeeb Mekkath²

¹College of Engineering, International University of Kuwait, Ardiya, Kuwait

²College of Integrative Studies, Abdullah Al Salem University (AASU), Block 3, Khaldiya, Kuwait

junais.mekkath@aasu.edu.kw

36504 atoms supercell



11650 atoms supercell

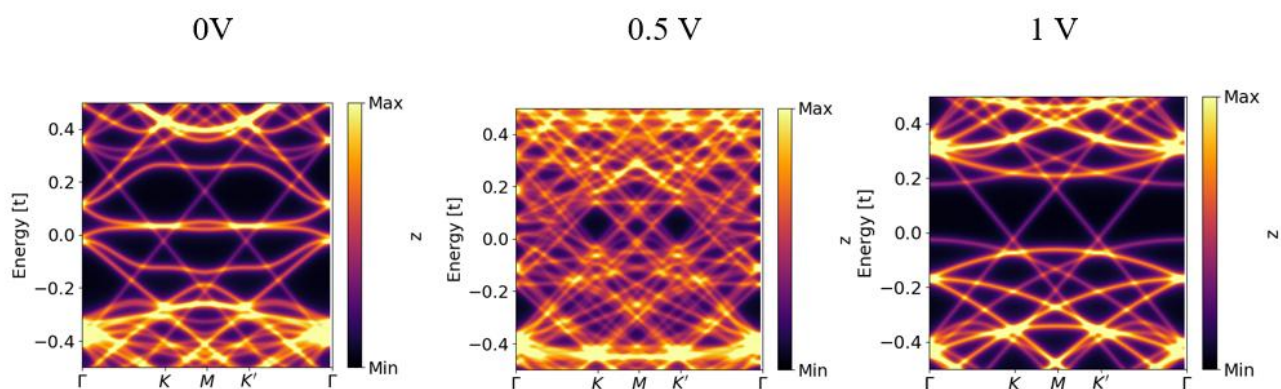


Figure S1: The comparative band structure results for two systems of different sizes considering interlayer bias. It is noticeable that the general trend in band structure evolution (in particular, localized and dispersive bands), as influenced by the interlayer bias, remains largely consistent (albeit with slight variations) as the system size increases.

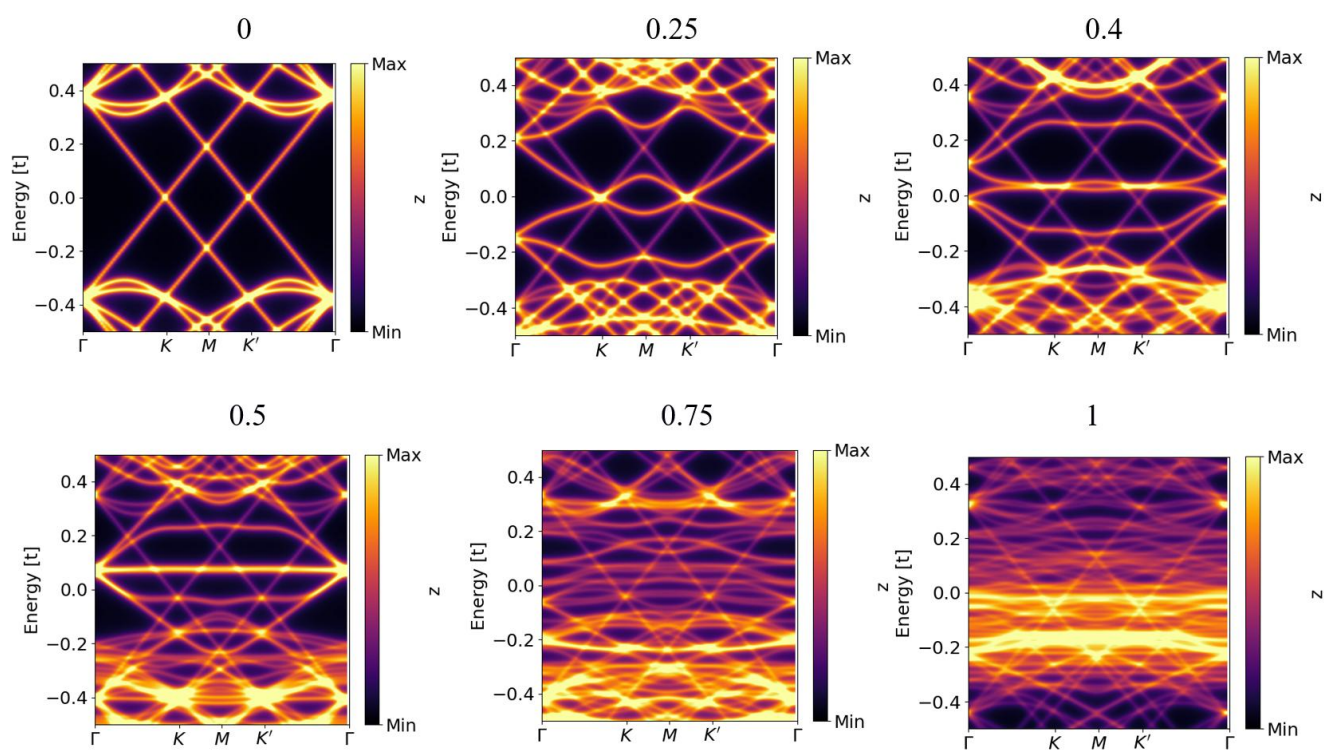


Figure S2: Band structure results depicting variations in interlayer hopping with a zero-interlayer bias. Flat bands emerge for a value of 0.4